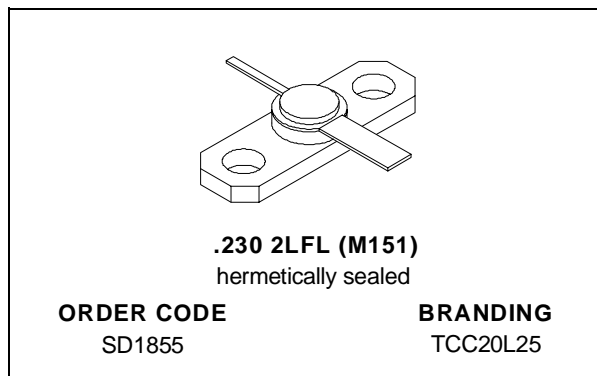


RF & MICROWAVE TRANSISTORS GENERAL PURPOSE LINEAR APPLICATIONS

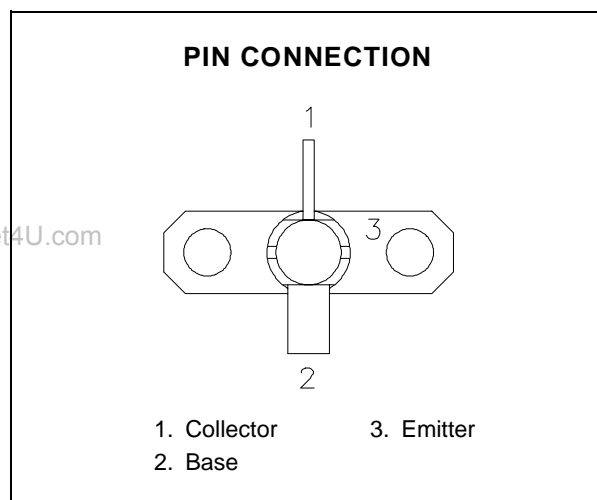
- 2.0 GHz
- 20 VOLTS
- CLASS A
- OVERLAY GEOMETRY
- GOLD METALLIZED DIE
- COMMON EMITTER CONFIGURATION
- $P_{OUT} = 2.5W$ MIN. WITH 6.0 dB GAIN



DESCRIPTION

The SD1855 is a silicon NPN planar transistor designed for high gain linear performance at 2.0 GHz. This part uses gold metallized die and polysilicon site ballasting to achieve high reliability and ruggedness. The SD1855 can be used for applications such as telecommunications, radar, ECM, space and other commercial and military systems.

DataSheet4U.com



DataShee

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CES}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	3.5	V
I_C	Device Current	0.5	A
P_{DISS}	Power Dissipation	20.6	W
T_J	Junction Temperature	+200	$^{\circ}C$
T_{STG}	Storage Temperature	- 65 to +150	$^{\circ}C$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	8.5	$^{\circ}C/W$
---------------	----------------------------------	-----	---------------

SD1855 (TCC20L25)**ELECTRICAL SPECIFICATIONS** ($T_{case} = 25^{\circ}C$)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_C = 2mA$	$I_E = 0mA$	40	—	—	V
BV_{CEO}	$I_C = 5mA$	$I_B = 0mA$	25	—	—	V
BV_{EBO}	$I_E = 2mA$	$I_C = 0mA$	3.5	—	—	V
h_{FE}	$V_{CE} = 5V$	$I_C = 400mA$	15	—	150	—

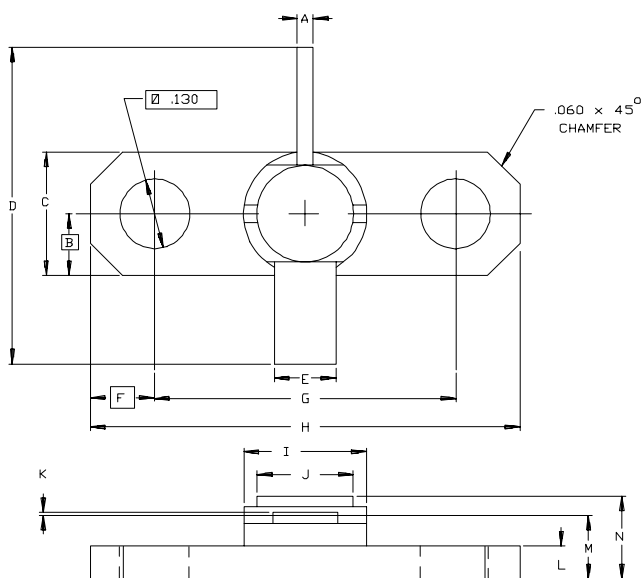
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}^*	$f = 2.0 GHz$	$V_{CE} = 20 V$	$I_{CQ} = 440 mA$	2.5	—	—	W
G_P^*	$f = 2.0 GHz$	$V_{CE} = 20 V$	$I_{CQ} = 440 mA$	6.0	—	—	dB

Note: * 1dB Compression

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0151



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.025/0,64	.035/0,89	K	.003/0,08	.007/0,18
B	.115/2,92	NDM.	L	.055/1,40	.067/1,70
C	.225/5,72	.235/5,97	M	.120/3,18	.140/3,56
D	.710/18,03	.750/19,05	N		.170/4,32
E	.110/2,79	.120/3,05			
F	.120/3,05	NDM.			
G	.555/14,10	.565/14,35			
H	.795/20,19	.805/20,45			
I	.222/5,64	.236/5,99			
J	.165/4,19	.185/4,70			

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A